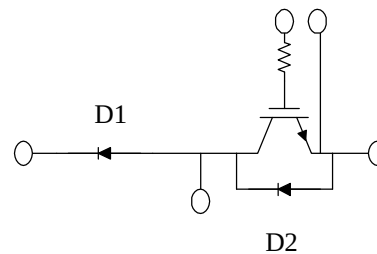


Description:

Powerex IGBT Hermetic modules are designed for use in switching applications. Each Module consists of two IGBT transistors in a half bridge configuration with each transistor having a reverse connected super fast recovery free wheel diode. All components are located in a hermetically sealed chamber and are electrically isolated from the heat sinking base plate, offering simplified system assembly and thermal management.

Features:

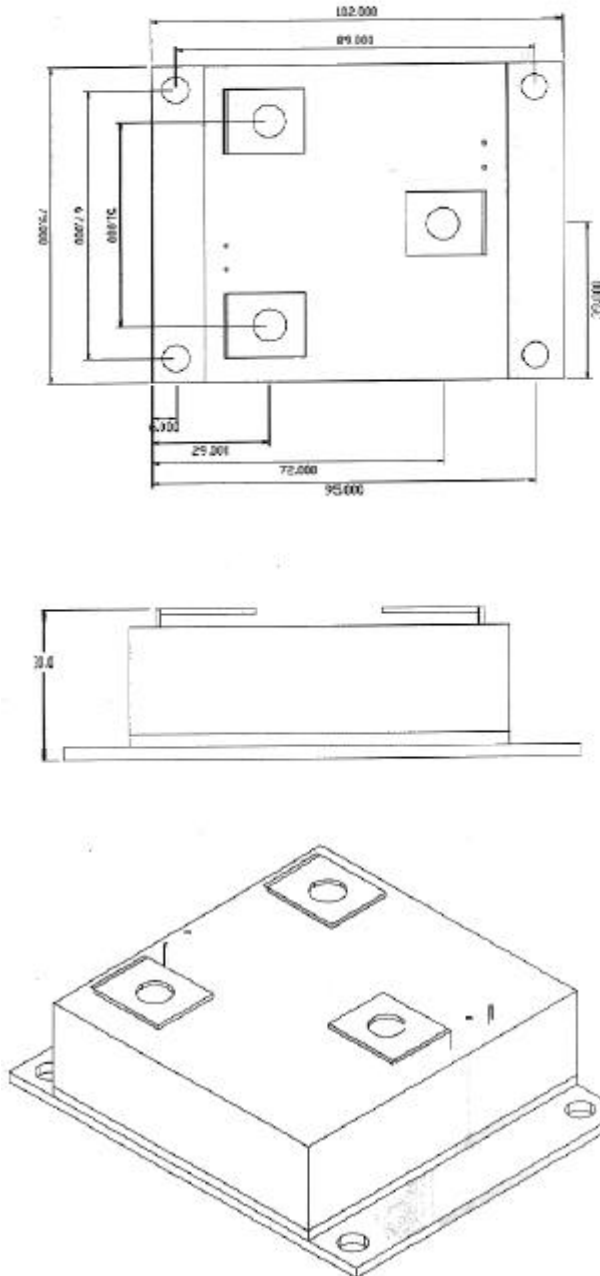
- ◆ Low Drive Power
- ◆ Low $V_{CE(sat)}$
- ◆ Discrete Super-Fast Recovery (70ns) Free-Wheel Diode
- ◆ Isolated Base plate for Easy Heat sinking
- ◆ Fully Hermetic Package
- ◆ Package Design Capable of Use at High Altitudes
- ◆ Package can be modified to adhere to customer dimensions.
- ◆ D1 sized to match RM400HA

Schematic:**Applications:**

- ◆ AC Motor Control
- ◆ Motion/Servo Control
- ◆ Air Craft Applications

Ordering Information:

Contact Powerex Custom Modules



Maximum Ratings, T_j=25°C unless otherwise specified

Ratings	Symbol		Units
Collector Emitter Voltage	V _{CES}	600	Volts
Gate Emitter Voltage	V _{GES}	±20	Volts
Collector Current	I _C	600	Amperes
Peak Collector Current	I _{CM}	1200*	Amperes
Diode Forward Current (D2)	I _{FM}	600	Amperes
Diode Forward Current (D1)	I _{FM}	400	Amperes
V Isolation	V _{RMS}	2500	Volts

Static Electrical Characteristics, T_j=25°C unless otherwise specified

Characteristic	Symbol	Test Conditions	Min	Typ	Max	Units
Collector Cutoff Current	I _{CES}	V _{CE} =V _{CES}			1.0	mA
Gate Leakage Current	I _{GES}	V _{CE} =0V			0.5	μA
Gate-Emitter Threshold Voltage	V _{GE(th)}	I _C =60mA, V _{CE} =10V	4.5	6.0	7.5	Volts
Collector-Emitter Saturation Voltage	V _{CE(sat)}	I _C =600A, V _{GE} =15V		2.1	2.8	Volts
	V _{CE(sat)}	I _C =600A, V _{GE} =15V, T _j =150°C		2.15		Volts
Total Gate Charge	Q _G	V _{CC} =300V, I _C =600A, V _{GS} =15V		1800		nC
Diode Forward Voltage (D1)	V _{FM}	I _E =400A, V _{GS} =0V			2.0	Volts
Diode Forward Voltage (D2)	V _{FM}	I _E =600A, V _{GS} =0V			2.8	Volts

Dynamic Electrical Characteristics, T_j=25°C unless otherwise specified

Characteristic	Symbol	Test Conditions	Min	Typ	Max	Units
Input Capacitance	C _{ies}	V _{GE} =0V			60	nF
Output Capacitance	C _{oes}	V _{CE} =10V			21	nF
Reverse Transfer Capacitance	C _{res}	f=1MHz			12	nF
Turn on Delay time	t _{d(on)}	V _{CC} =300V				nS
Rise Time	t _r	I _C =600A				nS
Turn off delay time	t _{d(off)}	V _{GE1} =V _{GE2} =15V				nS
Fall Time	t _f	R _G =1Ω			300	nS
Diode Reverse Recovery Time (D1)	t _{rr}	I _E =400A			400	nS
Diode Reverse Recovery Time (D2)	t _{rr}	I _E =600A			110	nS
Diode reverse Recovery Charge (D1)	Q _{rr}	di _E /dt=400A/μS		80		μC
Diode reverse Recovery Charge (D2)	Q _{rr}	di _E /dt=1200A/μS		1.62		μC

Thermal and Mechanical Characteristics, $T_j=25^\circ\text{C}$ unless otherwise specified

Characteristic	Symbol	Test Conditions	Min	Typ	Max	Units
Thermal Resistance, Junction to Case	$R_{\theta JC}$	IGBT			0.06	$^\circ\text{C/W}$
Thermal Resistance, Junction to Case	$R_{\theta JC}$	Diode (D1)			0.08	$^\circ\text{C/W}$
Thermal Resistance, Junction to Case	$R_{\theta JC}$	Diode (D2)			0.12	$^\circ\text{C/W}$

